100V P-Channel MOSFETs

General Description

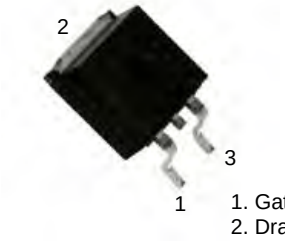
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-100V	45mΩ	-30A

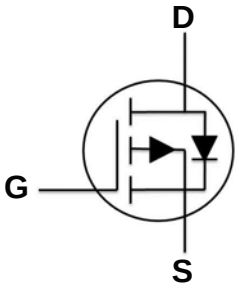
Features

- *-100V,-30A, RDS(ON) 45mΩ@VGS = -10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

TO-252 Pin Configuration



1. Gate
2. Drain
3. Source



Applications

- *Networking*
- *Load Switch*
- *LED applications*

Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (T_C=25℃)	-30	A
	Drain Current – Continuous (T_C=100℃)	-19	A
I_{DM}	Drain Current – Pulsed[1]	-120	A
EAS	Single Pulse Avalanche Energy[2]	180	mJ
IAS	Single Pulse Avalanche Current[2]	-60	A
P_D	Power Dissipation (T_C=25℃)	102	W
	Power Dissipation – Derate above 25℃	0.82	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.22	℃/W
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W

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Electrical Characteristics (T_J=25℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-80V , V_{GS}=0V , T_J=85℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=± 20V , V_{DS}=0V	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-15A	---	36	45	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	40	55	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	---	-2.5	V
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-5A	---	22	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=-50V , V_{GS}=-10V , I_D=-10A	---	98	150	nC
Q_{gs}	Gate-Source Charge[3,4]		---	16.2	30	
Q_{gd}	Gate-Drain Charge[3,4]		---	13.8	26	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=-50V , V_{GS}=-10V , R_G=25Ω I_D=-5A	---	58	105	ns
T_r	Rise Time[3,4]		---	24	50	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	215	450	
T_f	Fall Time[3,4]		---	94	180	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , F=1MHz	---	6315	9000	pF
C_{oss}	Output Capacitance		---	220	330	
C_{rss}	Reverse Transfer Capacitance		---	50	100	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-30	A
I_{SM}	Pulsed Source Current		---	---	-60	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=-50V,V_{GS}=-10V,L=0.1mH,I_{AS}=-60A.,Starting T_J=25℃
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

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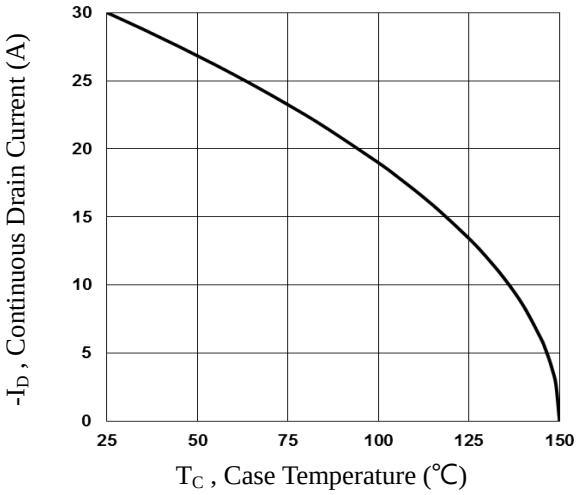


Fig.1 Continuous Drain Current vs. T_C

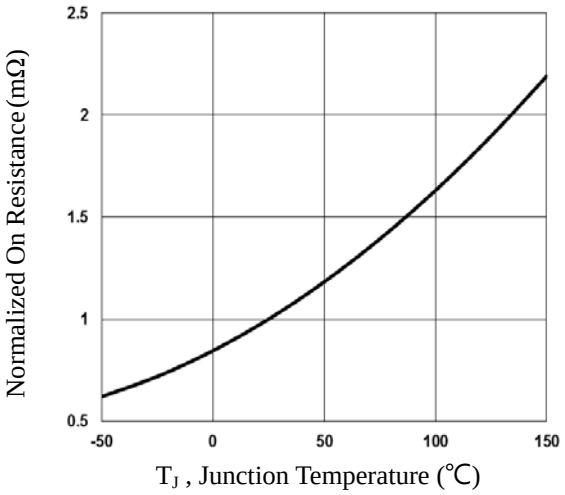


Fig.2 Normalized RDSON vs. T_J

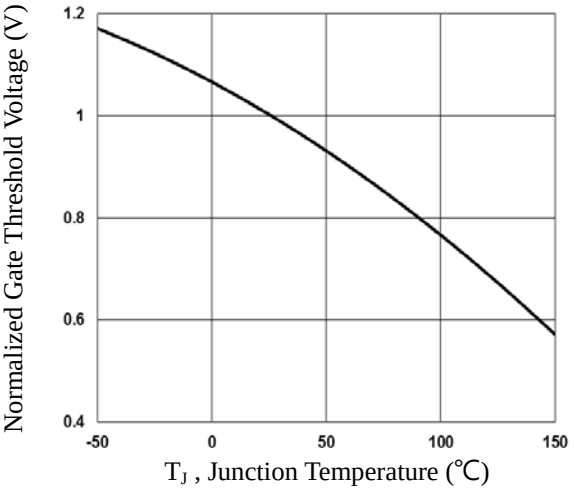


Fig.3 Normalized V_{th} vs. T_J

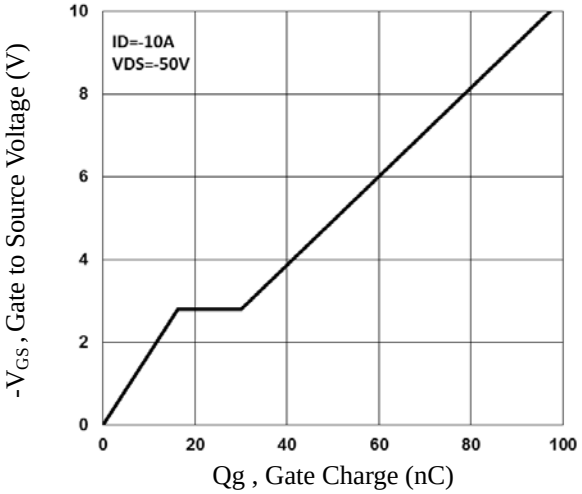


Fig.4 Gate Charge Waveform

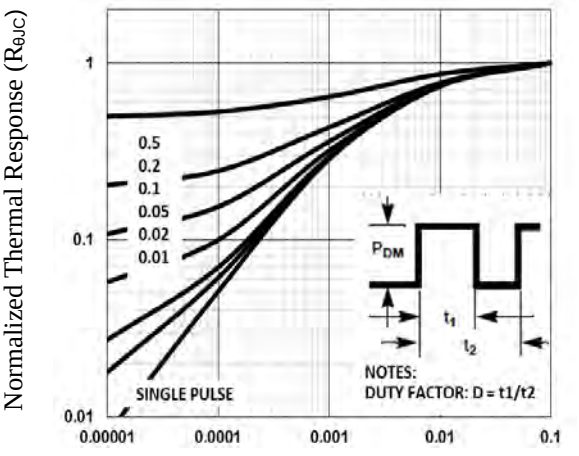


Fig.5 Normalized Transient Impedance

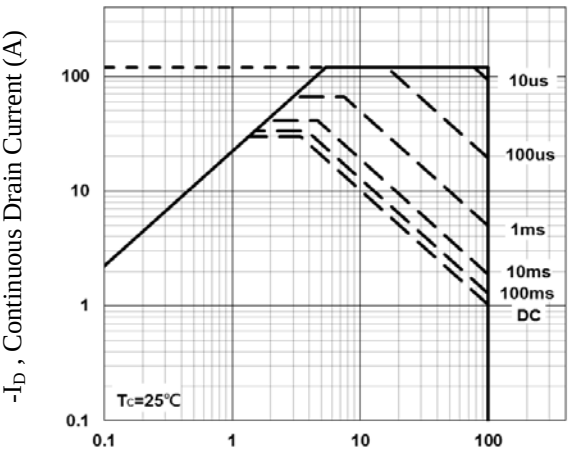


Fig.6 Maximum Safe Operation Area

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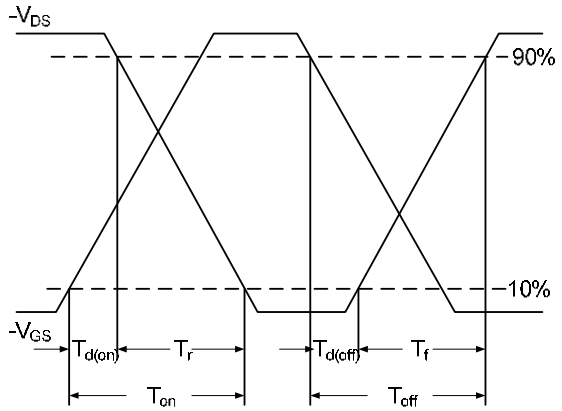


Fig.7 Switching Time Waveform

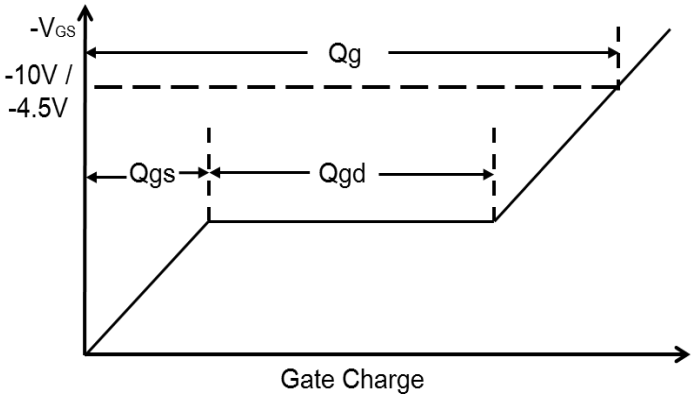
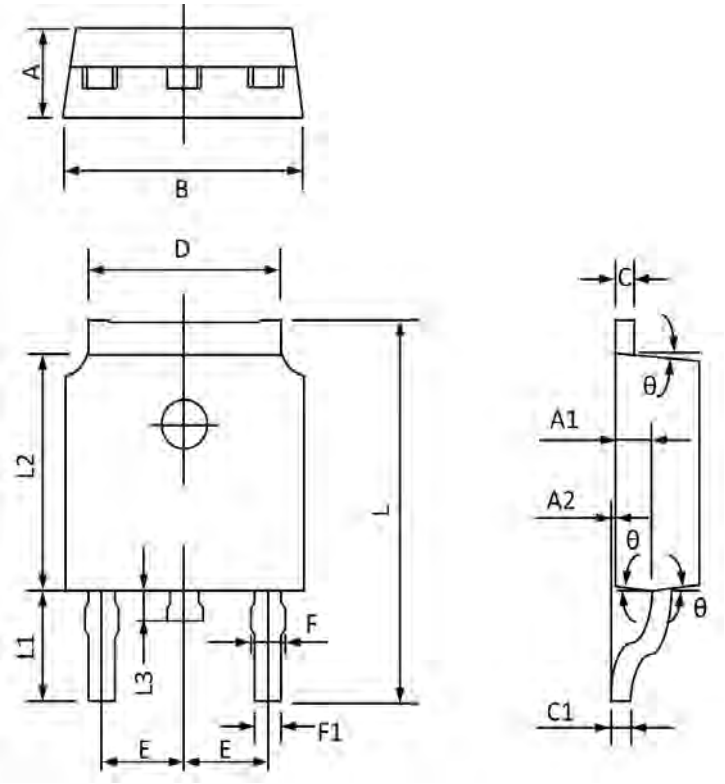


Fig.8 Gate Charge Waveform

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TO-252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.400	2.200	0.094	0.087
A1	1.110	0.910	0.044	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.400	0.268	0.252
C	0.580	0.450	0.023	0.018
C1	0.580	0.460	0.023	0.018
D	5.500	5.100	0.217	0.201
E	2.386	2.186	0.094	0.086
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.400	0.244	0.213
L3	1.200	0.600	0.047	0.024
θ	9°	3°	9°	3°